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Surface electric field driven directional charge separation on Ta₃N₅ cuboids enhancing photocatalytic solar energy conversion



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ABSTRACT

Enhancing the separation and transfer of photogenerated carriers is critical factor for increasing the light to chemical energy conversion efficiencies. Here, we exposed $\{001\}$ and $\{010\}$ facets on [100] oriented Ta_3N_5 cuboid, creating 18.6 times enhancement in photocatalytic reduction of CO_2 to CH_4 and a 0.42 V_{RHE} (reference to reversible hydrogen electrode) photocurrent onset potential for photoelectrochemical water splitting. The pronounced photocatalytic performance is mainly attributed to that surface electric field from large surface band bending of the $\{001\}$ with high work function drives electrons and holes to $\{010\}$ and $\{001\}$, respectively, achieving a spatial charge separation. Differing to a main effect in charge separation and transfer for the traditional junction electric field region at buried heterjunction or homojunction interface, a surface electric field region is a place where charges separate and transfer efficiently and also the place for the catalytic reactions to occur.

1. Introduction

Using the photocatalysis technique to convert carbon dioxide into hydrocarbons or split water into hydrogen fuels is an economical strategy for solving environmental concerns and energy shortages [1,2]. To apply this technique, an efficient photocatalyst with visible-light absorption and high quantum efficiency is urgently needed for largescale efficient conversion of solar energy into chemical energy [3-5]. Nevertheless, for many semiconductors with narrower band gaps, the low quantum efficiency remains a restriction in their practical applications owing to the high recombination of photogenerated carriers. Tantalum nitride (Ta₃N₅) photocatalyst with a band gap of 2.1 eV, absorbing a large proportion of the visible wavelength range of solar light (600 nm) with a theoretical solar-to-hydrogen (STH) conversion efficiency of 15.9%, is considered to be the promising candidate for photocatalytic and photoelectrochemical water splitting [6-9]. However, several unfavorable factors, such as both of heavy effective mass of photogenerated carriers and considerable crystal defects inducing unsatisfying separation and transfer of photogenerated carriers, severely constrained the photocatalyic performances regardless of the Ta₃N₅ powdered photocatalyst or photoanodes [10–12]. In order to improve the separation of photogenerated carriers, several accessible routes have been shown to be effective in reducing the charge recombination of Ta_3N_5 such as forming the built-in electric field by constructing heterojunction with other semiconductors [13–16] or passivating the surface states with a passivation layer [17,18]. Nevertheless, restrictions on energy level matching in heterojunction or high-quality interface for effectively passivating the surface states are still the challenge to the development of high-activity Ta_3N_5 .

Experimental and theoretical evidences have confirmed that 600 nm (2.06 eV) and 500 nm (2.48 eV) absorption edges coexist in the Ta_3N_5 films, which can respectively be ascribed to photon absorption along a-axis and (b, c)-axes crystallographic directions [19], and a lighter carriers effective mass was found along (b, c)-axes directions in comparison with a-axis [20]. This means that overcoming the drawbacks of Ta_3N_5 by constructing the a-axis oriented crystal structure, resulting in the shortened (b, c)-axes carriers migration distances, is highly reasonable to optimize the separation and transfer of carriers, thus enhancing the photocatalytic activity. Recently, much interest has been focused on semiconductor crystals with specific facets that induce the

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high reactive activities and high reactive selectivity [21]. It has been found that crystal facet engineering of several semiconductor metal oxides, such as TiO_2 [22,23], $BiVO_4$ [24–26], $SrTiO_3$ [27], CeO_2 [28], and Cu_2O [29], can achieve the anisotropic photogenerated charge transfer and accumulation, suppress carriers recombination, based on the different atomic construction and coordination between two adjacent facets. Attempts to deliberately fabricate such materials are challenged by the thermodynamic growth mechanisms of the crystals. Usually the selective adsorption of surfactants or ions on high-energy facets has been employed to suppress the growth rate along specific crystallographic direction [30]. However, the effects of Ta_3N_5 crystal facet on the photocatalytic reactions were barely concerned, due to its harsh preparation conditions of high-temperature ammonolysis.

Herein, with assistance of NaCl-NaF eutectic molten salt, we have prepared a [100] crystallographic-direction growth Ta₃N₅ cuboids with dominantly coexposed {001} and {010} crystal facets through the nitridation of NaTaO3 precursor. The Ta3N5 cuboids exhibited a marked improvement in photocatalytic reduction of CO2 to CH4 and a 0.42 VRHE photocurrent onset potential for photoelectrochemical water splitting. The pronounced photocatalytic performance is mainly attributed to that a large surface band bending forms at the high-work-function {001} facet, which drives directional drift of electrons and holes to {010} and {001}, respectively, achieving a spatial charge separation. Differing to a main effect in charge separation for a buried junction electric field region of heterjunction, a surface electric field region under a crystal facet with high work function not only contributes to the charge separation and transfer but also offers the catalytic reaction sites. The proposed new strategy to combining the facet engineering and the oriented crystal growth may promote a rational material design for efficient solar energy conversion.

2. Experimental methods

2.1. Preparation of $NaTaO_3$ precursor

The NaTaO $_3$ microcubes were prepared by a hydrothermal reaction. Typically, Ta $_2$ O $_5$ powder (1 mmol) was added to NaOH solution (30 mL, 1 M). After ultrasonic dispersion, the resultant suspension was poured into a 50 mL Teflon vessel and heated to 160 °C for 12 h. The obtained white powder was rinsed with deionized water thoroughly, and dried in an oven at 60 °C for 12 h.

2.2. Preparation of Ta₃N₅ samples

To synthesize [100] oriented Ta_3N_5 cuboids, the obtained $NaTaO_3$ microcubes were sufficiently mixed with NaCl-NaF (molar ratio of 2:1 for NaCl to NaF) mixed salts (molar ratio of 1:2 for NaTaO $_3$ to molten salts) in a methanol, and subsequently calcined in air at 823 K for 2 h. The as-prepared NaTaO $_3$ /NaCl-NaF powders (0.3 g) were heated at 1173 K for 7 h under flowing NH $_3$ (800 mL·min $^{-1}$). After natural cooling, the obtained product was washed several times with deionized water, and dried in an oven at 60 °C for 12 h. For comparison, using the same nitriding procedure, [100] oriented Ta_3N_5 nanorods with no specific exposed facets was prepared by nitriding NaTaO $_3$ microcubes (0.3 g) in NaCl molten salt (molar ratio of 1:2 for NaTaO $_3$ to NaCl) and conventional Ta_3N_5 particles were obtained by directly nitriding the Ta_2O_5 precursors (0.3 g).

2.3. Sample characterizations

The phase structure of as-synthesized samples was measured with X-ray powder diffraction (XRD, Rigaku Ultima III) using Cu K α radiation at 40 kV and 40 mA. The size and morphology of samples were observed by scanning electron microscope (SEM, Nova NanoSEM 230FEI Co) and field emission transmission electron microscope (TEM, JEM-200CX). Ultraviolet-visible (UV–vis) diffuse reflectance spectra were

obtained by a UV–vis spectrophotometer (UV-2550, Shimadzu) and corresponding absorption spectra calculated by a Kubelka-Munk equation. The Brunauer-Emmett-Teller (BET) surface area was measured using a surface area analyser (Micromeritics Tristar-3000, USA) at liquid nitrogen temperature (77 K). The amounts of CO₂ physisorbed on the Ta₃N₅ samples were evaluated by BET method at ice water temperature (273 K). The constituent of samples was characterized by X-ray photoelectron spectroscopy (XPS, Thermo ESCALAB 250). Photoluminescence (PL) spectra were measured by using a picosecond Ti:Sapphire laser (Mira HP, from Coherent) as the excitation source. The decay profiles of Ta₃N₅ samples were fitted by a biexponential function of $I(t) = A_1 \exp(-t/\tau_1) + A_2 \exp(-t/\tau_2)$, where I(t) is the fluorescence intensity at time t, A_1 and A_2 are the pre-exponential factor, and a_1 and a_2 are the lifetime.

2.4. Facet-selective photodeposition of noble metals or/and metal oxides

Typically, Ta_3N_5 powder (0.1 g), electron-reduced and/or hole-oxidized precursors with a 3Wt% weight ratio for products to Ta_3N_5 were mixed in deionized water for obtaining 100 mL suspension. The suspension was irradiated by 300 W Xe lamp ($\lambda \geq 420$ nm) with constant stirring for 5 h. The obtained products was filtered, washed with deionised water several times, and dried at 60 °C overnight. The photo-deposition of Pt, Au or Ag was carried out with H_2PtCl_6 (HAuCl₄, AgNO₃) as precursor, and 20 mL methanol as hole sacrificial agent. The photo-deposition of MnO_x or Co_3O_4 was carried out with MnSO₄ (Co (NO₃)₂) as the precursor, and NaIO₃ (2.0 g) as electron acceptor. The simultaneous photo-reduction and photo-oxidation deposition were achieved with dual precursors without addition of additional electron acceptor or hole sacrificial agent.

2.5. Photocatalytic CH4 evolution

Pt as a cocatalyst was loaded by following procedure. Ta₂N₅ powders (0.1 g), H₂PtCl₆ aqueous solution (3Wt% Pt, according to the weight ratio of Pt:Ta₃N₅) and CH₃OH solution (40 mL) were mixed in 60 mL deionized water. The suspension was then irradiated by 300 W Xe lamp ($\lambda \ge 420 \, \text{nm}$) with magnetically stirring for 5 h. In the photocatalytic reduction of CO₂, the Pt-loaded Ta₃N₅ powders (0.1 g) were homogeneously dispersed on a glass reactor with an area of 4.2 cm². The volume of the reaction system was about 230 mL and a 300 W Xe lamp ($\lambda \ge 420 \, \text{nm}$) was used as the light source for the photocatalytic reaction. After the reaction system was vacuum-treated several times, high-purity CO2 gas was introduced into the reaction to reach the ambient pressure. Deionized water (0.4 mL) was injected as a reducing agent into the reaction system. During irradiation, about 1 mL of gas was withdrawn from the reaction tank at a given interval and then subjected to CH₄ concentration analysis using gas chromatography (GC-2014, Shimadzu Corp, Japan). The apparent quantum yields (AQYs) for CO2 reduction were measured using the same experimental process, except that a different cut-off filter (Y50, > 500 nm) was employed. The apparent quantum efficiency (AQY) was estimated by formula of

$$AQY = \frac{8 \times number\ of\ CH_4\ molecules}{number\ of\ incident\ photons} \times 100\% \tag{1}$$

The number of photons reaching the catalyst was measured using a spectroradiometer (LS-100, EKO Instruments Co., LTD.). It was assumed that all incident photons were absorbed by the catalyst. The total number of incident photons in the wavelength range of 500–600 nm was estimated to be 2.36×10^{21} photon·h $^{-1}$.

2.6. Photoelectrochemical tests

The photoanodes were fabricated using an electrophoretic deposition (EPD) method followed by necking treatment. Typically, iodine (10 mg) and Ta_3N_5 (40 mg) powders were dispersed in acetone (50 mL)

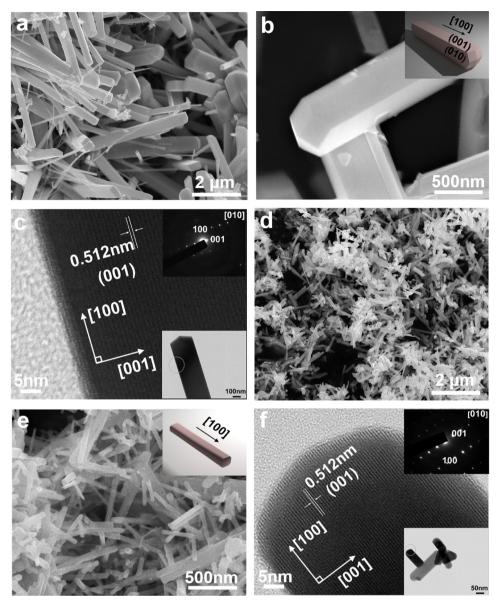


Fig. 1. SEM and HRTEM images for (a–c) Ta_3N_5 cuboids and (d–f) nanorods. Insets in Fig.1b and e show the schematic illustrations of cuboid and nanorod, respectively. TEM images of Ta_3N_5 cuboids and nanorods, and their corresponding SAED patterns were shown in insets of Fig. 1c and f, respectively.

with the assistance of sonication to obtain the Ta_3N_5 powder suspension for EPD. The EPD process for Ta_3N_5 was conducted between two parallel FTO electrodes with the distance of 1 cm under 15 V of bias for 5 min. The average thickness of film on FTO was about 5 μm , which was measured from the cross-sectional scanning electron microscopy image. The coated area of the Ta_3N_5 films was ca. 1 cm \times 1 cm. The electrodes were dried in air, and then dropped with $TaCl_5$ methanol solution (10 mM, 10 μL) for five times. Finally, the dropped electrodes were heated at 500 °C for 30 min in flowing NH $_3$ (500 mL min $^{-1}$).

The deposition of Co species cocatalysts on Ta_3N_5 photoanode was carried out by an impregnation method as the following procedures. The colloidal $Co(OH)_x$ solution was firstly prepared by the addition of NaOH solution $(30\,\mu\text{L},\ 1\,\text{M})$ into an aqueous solution of $Co(NO_3)_2$ (5 mL, 0.01 M). The Ta_3N_5 electrode was subsequently immersed into the as-prepared $Co(OH)_x$ colloidal solution for 1 h followed by washing with distilled water and then naturally dried in air at room temperature. Photoelectrochemical performance was measured in a three-electrode cell using an aqueous hydroxide electrolyte (1 M NaOH). A Ta_3N_5 film, Ag/AgCl electrode and a Pt foil were used as working electrode, counter electrode and reference electrode, respectively. An

AM1.5 G sunlight simulator (100 mW cm $^{-2}$, oriel 92251A-1000) was used as light source. Potentials of the working electrode were converted to a RHE (reversible hydrogen electrode) scale using the formula of $V_{\rm RHE} = V_{\rm Ag/AgCl} + 0.0591 \, \rm pH + 0.1976 \, V$. The electrochemical analyzer (Solartron 1260 + 1287) was used to measure electrochemical impedance spectra under 10 mV amplitude perturbuation and frequencies between 0.1 Hz and 10 MHz. Bulk charge separation efficiency $(\eta_{\rm sep})$ was calculated based on the equation:

$$J_{Na_2SO_3} = J_{\max} \eta_{abs} \eta_{sep} \eta_{trans} \tag{2}$$

 $(J_{max}:$ maximum theoretical photocurrent, $\eta_{abs}:$ light absorption efficiency, $\eta_{trans}:$ surface transfer efficiency). The η_{trans} was approximated as 100% when Na_2SO_3 solution was used as an electrolyte. As a consequence, the photocurrent density in the presence of Na_2SO_3 is obtained by:

$$J_{Na_2SO_3} = J_{\max} \eta_{abs} \eta_{sep} \tag{3}$$

The corresponding charge separation efficiency:

$$\eta_{sep} = J_{Na_2SO_3}/(J_{max}\eta_{abs})$$
(4)

2.7. Theoretical calculations

The DFT calculations are performed by the VASP code with the projected-augmented-wave (PAW) method. For the exchange-correlation functional, the generalized gradient approximation (GGA) in the scheme of Perdew-Bueke-Ernzerhof (PBE) is used. For N and Ta, the $2s^23p^3$ and $5p^65d^46s^1$ orbital, respectively, are treated as valence states. The cutoff energy for basis functional is 500 eV. The Ta_3N_5 (010) and (001) surfaces can be exposed by different terminations. The slab models used in this work have been proved to be the most stable terminations. For the (010) and (001) surfaces, the Γ -centered k-point meshes of $2\times 6\times 1$ and $5\times 5\times 1$, respectively, are adopted for the Brillouin zone integration. In addition, a stable structure to describe the oxygen atom replacing the nitrogen atom is estimated by calculating surface energies, and the most reliable slab model with O_N impurities is adopted.

3. Results and discussion

3.1. Flux-assisted nitridation route to Ta₃N₅ cuboids

Ta₃N₅ cuboids growing along the [100] crystallographic direction with exposed {010} and {001} facets were synthesized by nitriding NaTaO3 microcubes in eutectic molten salt of NaCl and NaF under flowing NH₃ (800 mL min⁻¹) at 1173 K for 7 h. For comparison, using the same procedure, [100] oriented Ta₃N₅ nanorods with no specific exposed facets were prepared by nitriding NaTaO3 microcubes in NaCl molten salt and conventional Ta₃N₅ particles were obtained by directly nitriding the Ta₂O₅ precursors. X-ray photoelectron spectroscopy (XPS) analysis (Fig. S1) indicated that the molten salt can be facilely eliminated by subsequent distilled water washing [31]. The Ta 4f XPS spectra were deconvoluted into four peaks: 26.0 eV for Ta 4f 5/2 and 24.2 eV for Ta 4f 7/2 in Ta₃N₅, and 27.2 eV for Ta 4f 5/2 and 25.4 eV for Ta 4f 7/2 in TaO_x species (Fig. S1a) [32,33]. Obviously, amount of TaO_x species is higher for the Ta₃N₅ particles than Ta₃N₅ nanorods and cuboids. This is attributed to the fact that replacing NaTaO3 by Ta2O5 as precursor in the synthesis of Ta₃N₅ will introduce more TaO_x species. As shown in Fig. 1a, b and S2a, the cuboid-like Ta₃N₅ crystal was about $5-10\,\mu m$ in length and $400\,n m$ in cross-section width. High-resolution transition electron microscope (HRTEM) images (Fig. 1c) showed that the spacing of lattice fringes paralleled to the longitudinal direction of Ta₃N₅ cuboid to be 0.512 nm, which can be assigned to the lattice pitch of (001) atomic plane [34,35]. Selected area electron diffraction (SAED) (inset of Fig. 1c) indicates that the cuboid is an uniform single crystal with the longitudinal direction along [100] and the width direction along [010] and [001]. The two major exposed surfaces of the cuboid were accordingly determined to be {010} and {001} facets. Comparatively, nitriding NaTaO3 microcubes in NaCl molten salt, the final product is [100] oriented Ta₃N₅ nanorods with uniform size of ~500 nm in length and ~20 nm in diameter (Fig. 1d-f). No clear facetexposed structure in Ta₃N₅ nanorods was observed by scanning electron microscope (SEM) images (Fig. 1d, e and S2b). As demonstrated in previous reports, Ta₃N₅ particles with unknown crystal orientation could be formed by directly heating NaTaO3 microcube layers coated on the Ta metal substrate at 1073 K in NH₃ flow [18,36,37]. In our case, addition of the molten salts, which induces a solvent effect during initial dissolution of mother-crystal NaTaO3 particles and subsequent recrystallization, is favorable to the a-axis oriented growth of Ta₃N₅ nanorods. Furthermore, compared with individual NaCl molten salt (melting point at 1074 K), the eutectic NaCl-NaF molten salt (melting point at 923 K) with lower melting point is favorable for stabilizing high-energy {010} and {001} facets, probably due to that the sufficient solvent environment facilitates the crystal growth and the co-adsorption of F and Cl species strongly changes the surface energy during the crystal growth in molten salt [38].

The X-ray diffraction (XRD) patterns of these as-prepared Ta₃N₅

samples were indexed to the single-phase orthorhombic structural Ta₃N₅ (JCPDS No. 19-1291) (Fig. S3). Notably, the diffraction intensity of (023) facet for Ta₃N₅ cuboids and nanorods was obviously higher than that of conventional Ta₃N₅ particles, suggesting that both the cuboids and nanorods were [100] oriented Ta_3N_5 crystal [19]. UV-vis absorption measurements (Fig. S4) indicated that the Ta₃N₅ cuboids, nanorods and particles have same absorption edge to be 600 nm, originating from the band gap excitation from N 2p orbitals to Ta 5d orbitals. Indeed, a slight step absorption is clearly visible at about 500 nm in the UV/Vis absorption spectra for [100] oriented Ta₃N₅ nanorods and cuboids, due to the prominent optical anisotropy in a-axis dominant Ta₃N₅ crystals [19]. An absorption peak was observed in 650-800 nm, resulting from the reduced tantalum defects [39]. Intensity of the defect absorption peak slightly decreased for both Ta₃N₅ cuboids and nanorods than particles, indicating that the molten salt growth is beneficial to reduce the crystal defects.

3.2. Photoreduction of CO2 into CH4 over Ta3N5 cuboids

The photocatalytic activities of these as-synthesized Ta₃N₅ cuboids, nanorods and particles with and without 3Wt% Pt cocatalyst were estimated by photoreduction of CO2 under the irradiation of a 300 W Xe lamp with a cut-off filter ($\lambda \ge 420 \text{ nm}$). As shown in Fig. 2a, Ta₃N₅ cuboids exhibited the highest CH4 generation rate to be $0.141\,\mu\text{mol}\,h^{-1}$, about 2.8 and 6.4 times higher than $0.051\,\mu\text{mol}\,h^{-1}$ for Ta_3N_5 nanorods and $0.022\,\mu\text{mol}\,h^{-1}$ for Ta_3N_5 particles, respectively. A CO2 reduction experiment performed in the dark or in the absence of the photocatalyst showed no appearance of CH₄, proving that the CO2 reduction reaction is driven by light with the photocatalyst. ¹³C isotope labeling was performed by GC-MS after irradiation of Ta₃N₅ under ¹³CO₂ atmosphere for 7 h. As shown in Fig. S5, clear ¹³CH₄ signal was observed in gaseous products, meaning that the CH₄ is indeed generated by CO2 reduction. After deposition of the Pt by photoreduction, the CH₄ generation rate over Ta₃N₅ cuboids reached up to $0.652\,\mu\text{mol}\,\text{h}^{-1}$, which is 3.7 and 18.6 times higher than Ta_3N_5 nanorods $(0.175 \,\mu\text{mol}\,\text{h}^{-1})$ and particles $(0.035 \,\mu\text{mol}\,\text{h}^{-1})$, respectively. The O_2 evolution rate was 1.31 μ mol h^{-1} , close to 2:1 M ratio of O_2 to CH₄, and very small amount of CO ($< 0.02 \,\mu\text{mol}\,\text{g}^{-1}$) and N₂ ($< 0.1 \,\mu\text{mol g}^{-1}$) were detected at the initial stage, which may be derived from the decomposition of the sample surface adsorption species. As described in the previous reports, the CH₄ is the observed main product for the gaseous CO2 reduction reaction [40,41]. This is probably attributed to that the CH4 is the most stable product, as well demonstrated in the degradation of alkane. In the case of degradation of alkane, a mixture of five different hydrocarbons CH₄, C₂H₄, C₂H₆, C₃H₆, and C₃H₈ was exposed to the photocatalyst in the presence of light and water vapor [3]. After 120 min of illumination, the hydrocarbons except CH4 degraded significantly. This indicated that the CH4 is more stable during the gaseous photocatalytic reaction. Other products such as the HCOOH or H2 were usually observed during the CO2 reduction on an electrode in liquid media due to the separated oxidation and reduction reaction chamber by proton exchange member [42]. However, for gaseous photocatalytic reaction, the oxidation and reduction reactions occur in the same reaction chamber, in which metastable reduced products were oxidized easy.

The apparent quantum yields (AQYs) of Ta_3N_5 particles, nanorods and cuboids photo-loaded with the Pt cocatalyst (3Wt%) were estimated to be 0.06%, 0.3% and 1.1% at 500 nm, respectively. This confirms a fact that the Ta_3N_5 cuboids present a high activity in CO_2 reduction. The specific surface area was determined by Brunauer-Emmett-Teller (BET) method to be $11.1~m^2g^{-1}$ for Ta_3N_5 particles, about 2 times higher than $5.4~m^2g^{-1}$ for Ta_3N_5 cuboids and $6.6~m^2g^{-1}$ for Ta_3N_5 nanorods. This indicated that the difference in photocatalytic performance among the three Ta_3N_5 samples can not be attributed to the difference in specific surface area. The amount of CO_2 physisorbed on the Ta_3N_5 cuboids was evaluated by BET method at 273 K to be

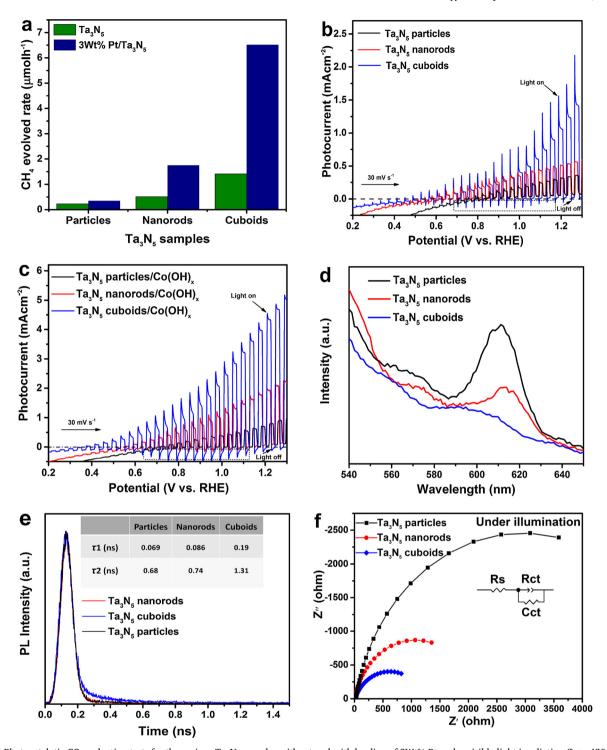


Fig. 2. (a) Photocatalytic CO_2 reduction tests for the various Ta_3N_5 samples without and with loading of 3Wt% Pt under visible light irradiation ($\lambda \ge 420$ nm). Light source: 300 W Xenon lamp. Photocatalysts: 0.1 g. (b, c) Current-potential curves for the various Ta_3N_5 electrodes without and with the modification of $Co(OH)_x$. (d) Photoluminescence spectra of synthesized Ta_3N_5 samples with an excitation wavelength of 450 nm. (e) Time-resolved transient PL decay of Ta_3N_5 samples. (f) Electrochemical impedance (EIS) analysis of the as-prepared Ta_3N_5 samples under UV–vis light illumination (300 W Xe lamp). Inset shows the equivalent circuit. R_s , R_{cb} and C_{ct} are the resistance from electrolyte and semiconductor-substrate electrical connection, interfacial charge transfer resistance between semiconductor and electrolyte, and the circuit capacitance, respectively.

 $0.31~mg~m^{-2}$, which is similar to $0.29~mg~m^{-2}$ for Ta_3N_5 nanorods and is about 3 times higher than $0.11~mg~m^{-2}$ for Ta_3N_5 particles, respectively (Fig. S6 and Table S1). Therefore, preferential adsorption of CO_2 and low defect states for flux-assisted grew Ta_3N_5 cuboids and nanorods may contribute to their higher CO_2 reduction ability than Ta_3N_5 particles. However, the similar adsorption of CO_2 and defect density on Ta_3N_5 cuboids and nanorods can not induce their big performance

differences in CH₄ generation.

3.3. Photoelectrochemical tests showing the separation efficiency of Ta_3N_5 cuboids

In order to further discover the nature of enhancement in photocatalytic performance of Ta_3N_5 cuboids, the three as-prepared Ta_3N_5

samples were respectively deposited on the fluorine-doped tin oxide (FTO) substrate using electrophoretic (EP) deposition technique with post-necking treatment with TaCl₅ to form effective contacts between the Ta₃N₅ crystal particles [43]. The as-prepared Ta₃N₅ photoanodes were then evaluated for photoelectrochemical water splitting in 1 M NaOH electrolyte (pH 13.6). As shown in Fig. 2b, the anodic photocurrents of Ta₃N₅ cuboids, nanorods and particles were observed at around 0.67, 0.66 and 0.86 V_{RHE} , and reached 1.37, 0.54 and 0.32 mA cm⁻² at 1.23 V_{RHE}, respectively. After depositing Co(OH)_x as water oxidation cocatalyst (Fig. S7), the detected anodic photocurrents of Ta₃N₅ cuboids/Co(OH)_x and Ta₃N₅ nanorods/Co(OH)_x were about 5 and 2.2 times increase than that of Ta₃N₅ particles/Co(OH)_x (0.94 mA ${\rm cm}^{-2}$ at 1.23 ${\rm V}_{\rm RHE}$), reaching 4.68 and 2.11 mA cm⁻² at 1.23 ${\rm V}_{\rm RHE}$, respectively (Fig. 2c). And the photocurrent onset potential of cuboid/ $Co(OH)_x$ electrode shifted to 0.42 V_{RHE} , which is much lower than 0.75 V_{RHE} for Ta₃N₅ particles/Co(OH)_x and 0.61 V_{RHE} for the nanorods/Co (OH)_x. Generally, the high onset potential can be attributed to many factors, such as the unsatisfying light absorption, low interfacial charge injection efficiency and the inefficient carrier separation and transport. In our case, the water oxidation cocatalyst, Co(OH)x, was used to improve the charge injection efficiency [7,8], and there are no obvious differences in the light absorption between the nanorods and cuboids (Fig. S4). The bulk charge separation efficiency (η_{sep}) was measured in 0.1 M Na₂SO₃ solution (pH was buffered to 7.5) (Fig. S8), both Ta₃N₅ electrodes with and without modification of Co(OH)x presented an obvious order of cuboids > nanorods > particles. In a wide potential range of 0.6-1.2 V_{RHE}, charge separation efficiency of cuboids is about 2 times higher than that of nanorods. Meanwhile, in order to exclude the TaCl₅ in the process of necking treatment may affect the spatial charge separation of the particle itself. The photocurrent activities over the various Ta₃N₅ electrodes were estimated without necking treatment and with TiCl4 treated, respectively (Fig. S9). The same change trend between η_{sep} and photocurrent activity probably meaning that the high activity of Ta₃N₅ cuboids would originate from their high charge separation efficiency.

It is noteworthy that the cross-section width of Ta₃N₅ cuboids is about 20 times larger than the diameter of Ta₃N₅ nanorods (Fig. 1b, e). Under the back-side (from FTO, holes travel through the semiconductor layer to semiconductor-liquid interface) and front-side illumination (from semiconductor, electrons travel through the semiconductor layer to FTO substrate) on Ta₃N₅ cuboids or nanorods electrode, no obvious photocurrent difference was observed, revealing an excellent charge transfer among these crystals (Fig. S10). Therefore, the enhanced activity for Ta₃N₅ cuboids than nanorods can not be attributed to the decreased grain boundaries in the Ta₃N₅ cuboids electrode with big crystal size. The electrochemical active surface area (ECSA) was estimated by using electrocapacitive measurements (Fig. S11). Ta₃N₅ nanorods and cuboids electrodes show similar ECSA, and are both lower than Ta₃N₅ particles, which is in good agreement with the BET measurements. According to the formula $a = B_i(hv - E_g)^2/hv$ (a is the absorption coefficient, hv is the incident photon energy, and Bi is the absorption constant), the band gaps of Ta₃N₅ particles, nanorods and cuboids are estimated to be 2.06 eV (Fig. S12a). The valence band maximum of the three Ta₃N₅ samples are measured to be similar (Fig. S12b), thus the synthesized Ta₃N₅ samples with different structures have the same conduction band minimum and valence band maximum. The photoluminescence (PL) spectra revealed that the Ta₃N₅ cuboids exhibited the lower band edge recombination with an emission peak at about 610 nm than Ta₃N₅ nanorods and particles (Fig. 2d), probably meaning that either the longer lifetime of the photogenerated charges with the slower recombination process or shorter lifetime of the photogenerated charges with the faster migration process. As seen in Fig. 2e, the PL decay curves of these samples were mathematically fitted by a biexponential model (Supporting information for details). In the inset table of Fig. 2e, the short lifetime τ_1 is usually attributed to the nonradiative recombination of the free excitions with surface defects,

and the long lifetime τ_2 is assigned to the radiative pathway from the recombination of photogenerated electrons and holes [44]. Relative to the Ta_3N_5 particles ($\tau_2=0.68\,\mathrm{ns}$) and nanorods ($\tau_2=0.74\,\mathrm{ns}$), the transient PL decay trace of the Ta_3N_5 cuboids demonstrates that PL lifetime (τ_2) is prolonged to $\sim 1.31\,\mathrm{ns}$, indicating that the crystal facet exposure on Ta_3N_5 cuboid may present strong positive association with its high charge separation ability which restrains the recombination of charges, achieving the longer survival time of the charges. Indeed, electrochemical impedance spectroscopy (EIS) measurement under irradiation showed an obvious decrease in semicircle diameter for cuboids than nanorods, indicating that the Ta_3N_5 cuboids have more excellent electrical conductivity due to the promoted charge separation and transfer (Fig. 2f).

3.4. Photodeposition to visualize the directional charge transfer

To further confirm the charge spatial separation, selective photodeposition of cocatalysts were also performed. The effect of directional charge transfer was verified based on the following mechanisms [24,26]:

The generation of photo-induced carriers,

Semiconductor +
$$nhv \rightarrow n(h^+ + e^-)$$
 (5)

For photoreduction deposition,

$$A^{n+} + ne^- \rightarrow A^0 \tag{6}$$

$$\frac{n}{2}H_2O + nh^+ \to \frac{n}{4}O_2 + nH^+ \tag{7}$$

For photooxidation deposition,

$$B^{m+} + (n+m)OH + nh^{+} \to BO_{n+m} + (n+m)H^{+}$$
 (8)

$$nH^{+} + \frac{n}{6}IO_{3}^{-} + ne^{-} \rightarrow \frac{n}{6}I^{-} + \frac{n}{2}H_{2}O$$
 (9)

Where, A is the noble metal (Pt, Ag, Au...) for reduction and B is the metal (Mn, Co...) for oxidation.

Photoreduction deposition of Pt particles for visualizing the electron transfer demonstrated that a majority of Pt particles were evidently deposited on the two symmetric surfaces among four exposed facets of Ta₃N₅ cuboid. Contrarily, photooxidation deposition of MnO_x to visualize the hole transfer mainly distributed on the another two symmetric surfaces of cuboid. A codeposition experiment indicated that MnO_x and Pt particles were respectively formed on two adjacent facets (Fig. S13). When using Au³⁺ and Co²⁺ to replace Pt⁴⁺ and Mn²⁺, respectively, similar experimental phenomena were still observed, further indicating that the light-driven selective deposition does not depend on the type of ion precursors (Fig. 3). These evidences proved that the photogenerated carriers selectively accumulated on the specific facets. Effective mass of electrons and holes towards [010] and [001] directions has been calculated, respectively, and demonstrated a slight difference in their mobility [20]. Therefore, the directional charge transfer can not be attributed to the difference in charge mobility.

3.5. The nature of spatial charge separation in Ta₃N₅ cuboids

Surface potential distribution on two adjacent facets of ${\rm Ta_3N_5}$ cuboid was detected by using Kelvin probe force microscope (KPFM) to measure contact potential difference (CPD) between a conducting tip and the sample [45]. Therefore, for a semiconductor, the CPD is defined as

$$V_{CPD} = (\phi_{sample} - \phi_{tip})/e \tag{10}$$

(where ϕ_{sample} and ϕ_{tip} are the work functions of the sample and tip, and e is the electronic charge), would be related to the space charge regions beneath the surfaces. As shown in Fig. 4, it is obvious that there is a more positive surface potential on a facet of Ta_3N_5 cuboid than its

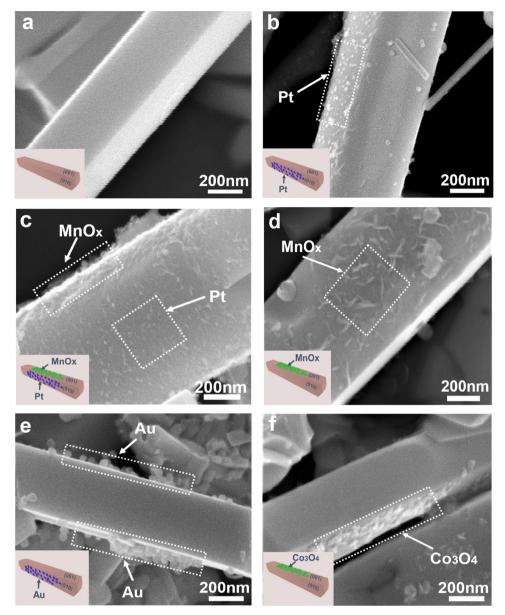


Fig. 3. SEM images for Ta_3N_5 cuboids with and without cocatalysts photodeposited. (a) Ta_3N_5 , (b) Pt/Ta_3N_5 , (c) $Pt-MnO_x/Ta_3N_5$, (d) MnO_x/Ta_3N_5 , (e) Au/Ta_3N_5 and (f) Co_3O_4/Ta_3N_5 .

adjacent side facet. This implies that the two adjacent facets exhibited the different surface work functions, thus inducing the different surface band bending for the ideal surface. As a consequence, it is reasonably suggested that the fabricated crystal-facet architecture was potentially responsible for the unusual enhancement in charge separation efficiency of Ta_3N_5 cuboids.

The theoretical simulations revealed that a stable (010) and (001) surface on orthorhombic Ta_3N_5 was composed of the N-Ta tetrahedron and octahedron units, respectively. As can be seen in the slab models of the {010} and {001} surfaces (Fig. S14), the surface atomic construction of {001} is flatter than that of {010}, and N atoms on the top layer of the {010} surfaces are all five-coordinated in contrast to {001} surfaces with only 50% five-coordinate N atoms. As demonstrated in our previously theoretical and experimental results [46–48], inevitable surface oxygen-related defects naturally occur during the synthetic process of Ta_3N_5 due to its thermodynamic instability. Indeed, X-ray photoelectron spectroscopy confirmed that lattice oxygen with about 0.3:1 atomic ratio of O to Ta exists on the surface of Ta_3N_5 , maybe locate at the nitrogen sites (O_N) (Table S2). Density functional theory

(DFT) calculations on the slab models of $\{001\} + O_N$ and $\{010\} + O_N$ surfaces indicated that introduction of the O_N makes the Fermi level in the band gap of clean $\{010\}$ surface moves to the conduction band of $\{010\} + O_N$ surface and the Fermi level at valence band of $\{001\}$ surface enter band gap of $\{001\} + O_N$ (Fig. 5a and S15). Generally, owing to an extremely low defect transition energy, the O_N impurities as the electron donors is able to reduce Ta, resulting in the conduction band downshift for $\{010\} + O_N$ than $\{010\}$ facet. However, no obvious conduction band shift was observed for $\{001\} + O_N$ referring to $\{001\}$ facet. This is because that the electrons donated by O_N have been compensated by the surface states of $\{001\} + O_N$ and no more electrons can reduce the Ta atoms, as indicated by that the surface states of the clean $\{001\}$ surface is located above the Fermi level.

Oxygen impurities changing the electronic structures of $\{010\}$ and $\{001\}$ facets also affects their work functions. Surface potential analysis demonstrated that the work function of $\{010\} + O_N$ and $\{001\} + O_N$ surfaces is about 3.86 and 5.34 eV, respectively, both them are lower than 6.28 eV for clean $\{010\}$ and 5.55 eV for clean $\{001\}$ surface (Fig. 5b–e), resulting from their inherent differences in atomic

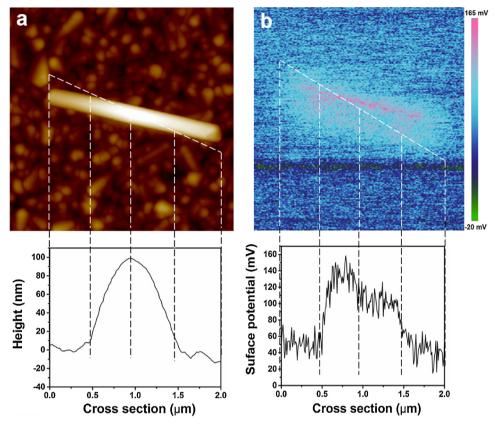


Fig. 4. (a) Topographic image of single Ta_3N_5 cuboid on FTO substrate. (b) The surface potentials were shown in color scale, and the pink regions represent the higher surface potential.

construction. Given that Fermi level position of bulk Ta_3N_5 is near -4.15 eV [49], the surface band bending upward was formed at interface between both {010} and {001} surfaces and the bulk for thermodynamic equilibrium, similar to the formation of Schottky junction. After introduction of O_N , such a band bending originated from difference in surface-bulk work function and can also be achieved at interface region between $\{001\} + O_N$ surface and bulk. In contrast, the work

function of $(010) + O_N$ is much close to that of bulk Ta_3N_5 , suggesting that there is no obvious space charge region on the surface of $\{010\} + O_N$. A facet with higher work function would induce a bigger surface band bending due to that exposed facets would share the same bulk Fermi level. Therefore, we believe that band bending upward of $\{001\}$ facet is much higher than that of $\{010\}$ facet due to its high work function, that is, a more striking built-in electric field in space charge

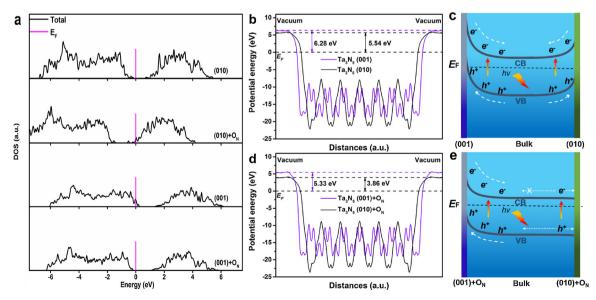


Fig. 5. (a) Theoretical calculated density of states (DOS) plots for (010), (001), $(010) + O_N$ and $(001) + O_N$ surfaces of Ta_3N_5 . (b) Potential diagrams of (010) and (001) surface based on the first-principles simulation (E_F denotes the Fermi level). (c) Schematic diagram of the surfaces band bending in the ideal case of clean surface model. (d) Potential diagrams of $(010) + O_N$ and $(001) + O_N$ surfaces based on the first-principles simulation. (e) Schematic diagram of the surface band bending on the $(010) + O_N$ and $(001) + O_N$ surfaces.

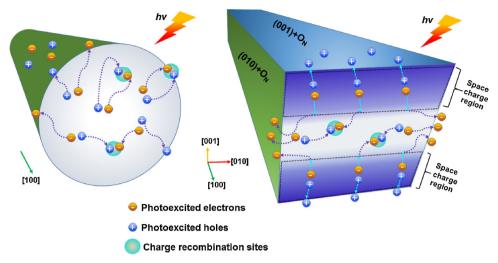


Fig. 6. A scheme to describe the behaviors of carriers migration in Ta_3N_5 nanorod and effect of electric field region on Ta_3N_5 cuboid contributing the spatial charge separation.

region beneath {001} facet drives the directional hole accumulation on {001} surface and the electron drift toward its adjacent {010} surface. A small band bending upward for {010} surface will be easily flatted by photoelectrons generated under illumination, and the photoelectrons from space charge region of {001} facet would further enlarge the effect of flatting band bending, thus benefiting to the electron accumulation on {010} surface. Obviously, such a directional charge transfer from {001} + O_N to {010} + O_N is more easy to realize, owing to no obvious barrier on the {010} + O_N facet to hinder the migration of electrons. This means that the oxygen defects provide a positive effect to the spatial separation of charges. In contrast, Ta_3N_5 nanorod without exposed specific facets would exhibit no obvious difference in its surface band bending, even the surface oxygen defects were introduced (Fig. 6).

Fig. 7a and b show the time course of CH₄ generation over various Ta₃N₅ samples. The photocatalytic activities of Ta₃N₅ cuboids remain almost unchanged after four reaction cycles, whereas the Ta₃N₅ nanorods and particles can only maintain 63% and 60% of their initial performances at third cycle. And the 2:1 M ratio of O2 to CH4 was well kept for each cycling reaction. XPS analysis was employed to further investigate the surface chemical states of the three samples after photoreduction reaction. As shown in Fig. 7c and S1b, for both Ta₃N₅ nanorods and particles, the relative intensity of the Ta 4p peaks increased after illumination while intensity of the N1 s peak decreased. The N/Ta changes in XPS spectra indicated that the Ta₃N₅ nanorods and particles suffer from severe self-oxidation process by photogenerated holes which are not delivered to the surface of catalyst in time to participate in the photocatalytic reaction. As for Ta₃N₅ cuboids, the formed built-in electric field beneath $(001) + O_N$ facet drives the hole migration from bulk to surface fast, which effectively limits this self-oxidation process. The $(010) + O_N$ and $(001) + O_N$ facets have different work functions, which means that Pt deposition on different crystal faces will affect the electron behavior of metal-semiconductor interfaces. The Pt particles (3Wt%) were also deposited on the surface of Ta_3N_5 by impregnation approach that normally results in random dispersion [24,27]. Compared with the Ta₃N₅ particles and nanorods, the photocatalytic activity in Fig. 7d is obviously decreased when the Pt cocatalyst was randomly deposited on the crystal facets of Ta₃N₅ cuboids. Actually, when the work function of a metal is greater than that of an n-type semiconductor, a Schottky junction can be established after close metalsemiconductor contact, and accelerates effectively the transfer of electrons from the semiconductor to the metal [29]. As seen in Fig. 7e, the potential of Pt is approximately 1.8 V lower than that of Ta₃N₅ (010) $+O_N$ facet and close to that of Ta_3N_5 (001) $+O_N$ facet, which means that the n-type Schottky junction can be constructed to accelerate the transfer of photogenerated electrons at Ta_3N_5 (010) + O_N -Pt interface rather than Ta_3N_5 (001) + O_N -Pt interface (Fig. 7f). Therefore, the CO_2 reduction activities of Ta_3N_5 cuboids with different deposition method of Pt cocatalyst show significant differences, which exactly proves the above-mentioned theoretical simulations.

Although the significant difference in surface band bending is greatly contributing to the enhancement in charge separation, the directional charge transfer behavior may induce an undesirable back electron transfer in an electrode that was composed of randomized Ta₃N₅ cuboids. A single-particle electrode model was adopted for easily understanding. As shown in Fig. S16, owing to the geometric symmetry of electron or hole gathering surface on Ta₃N₅ cuboid, if an electron gathering surface of the Ta₃N₅ cuboid contacted with the FTO conductive substrate, electron transfer from semiconductor to FTO will not be hindered. On the contrary, the electron transfer is restricted when a hole gathering surface contacted with the FTO substrate, which may induce a portion of electrons to migrate to the lateral surface of the cuboid to participate in an undesirable reduction reaction. Both the two electron transfer processes randomly existed in the Ta₃N₅ cuboids electrode. Indeed, a significant cathodic current on Ta₃N₅ cuboids electrode was observed at a wide applied potential range of 0.6-1.2 V_{RHE} (Fig. 2b, c), which may indicate that a small portion of the electrons is not facilely transferred to the FTO but involved in a oxygen reduction reaction (Fig. S16).

4. Conclusions

In summary, the [100] crystal-oriented Ta_3N_5 cuboids with dominant coexposed $\{010\}$ and $\{001\}$ lateral plane was prepared by nitriding reaction with assistance of molten salts and exhibited a significant improvement in photoreduction of CO_2 and photoelectrochemical water splitting. Exposing $\{001\}$ facets with high work function on Ta_3N_5 cuboid to induce a significant surface band bending, and transferring charges along brachydiagonal direction were effectively to facilitate the spatial separation of photoinduced charges. This work may provide a new strategy for developing more efficient transition metal nitride photocatalysts with visible light absorption based on semiconductor nanocrystal engineering.

Conflict of interest

The authors declare no competing financial interest.

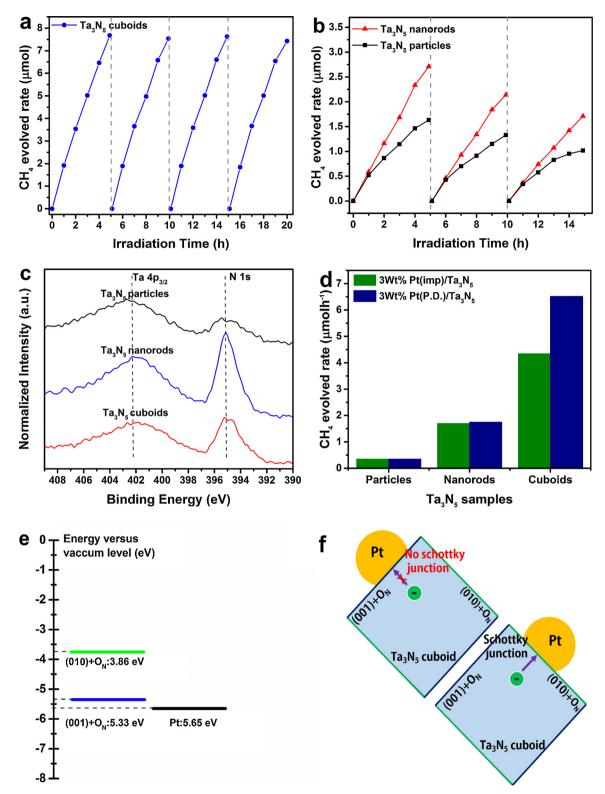


Fig. 7. Time course of CH₄ evolution under irradiation of a 300 W Xe lamp ($\lambda \ge 420$ nm) over (a) Ta_3N_5 cuboids, (b) Ta_3N_5 nanorods and particles. (c) Ta 4p and N 1 s XPS spectra of Ta_3N_5 samples after illumination for 14 h. (d) CH₄ generation over Ta_3N_5 samples with loading of 3Wt% Pt (Impregnation method noted as Pt (imp)/ Ta_3N_5 and photodeposition method noted as Pt(P.D.)/ Ta_3N_5). (e) Surface potential positions of Ta_3N_5 (001) + O_N and (010) + O_N and the Fermi level position of Pt. (f) Illustration for the charge transfer in the cross section of Ta_3N_5 cuboids with Pt deposited on (001) + O_N and (010) + O_N facets.

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Appendix A. Supplementary data

Supplementary material related to this article can be found, in the online version, at doi:https://doi.org/10.1016/j.apcatb.2018.06.036.

References

- [1] M. Walter, E. Warren, J. McKone, S. Boettcher, Q. Mi, E. Santori, N. Lewis, Chem. Rev. 110 (2010) 6446–6473.
- [2] M. Yan, Y. Hua, F. Zhu, W. Gu, J.H. Jiang, H.Q. Shen, W.D. Shi, Appl. Catal. B: Environ. 202 (2017) 518–527.
- [3] C. Li, G. Chen, J. Sun, J.C. Rao, Z.H. Han, Y.D. Hu, W.N. Xing, C.M. Zhang, Appl. Catal. B: Environ, 188 (2016) 39–47.
- [4] S. Kohtania, M. Koshiko, A. Kudo, K. Tokumura, Y. Ishigaki, A. Toriba, K. Hayakawa, R. Nakagaki, Appl. Catal. B: Environ. 46 (2003) 573–586.
- [5] Z. Zou, J. Ye, K. Sayama, H. Arakawa, Nature 414 (2001) 625-627.
- [6] P. Zhang, J. Zhang, J. Gong, Chem. Soc. Rev. 43 (2014) 4395-4422.
- [7] M. Liao, J. Feng, W. Luo, Z. Wang, J. Zhang, Z. Li, T. Yu, Z. Zou, Adv. Funct. Mater. 22 (2012) 3066–3074.
- [8] M. Li, W. Luo, D. Cao, X. Zhao, Z. Li, T. Yu, Z. Zou, Angew. Chem. Int. Ed. 52 (2013) 11016–11020
- [9] K. Ueda, T. Minegishi, J. Clune, M. Nakabayashi, T. Hisatomi, H. Nishiyama, M. Katayama, N. Shibata, J. Kubota, T. Yamada, K. Domen, J. Am. Chem. Soc. 137 (2015) 2227–2230
- [10] J. Morber, I. Narkeviciute, T. Jaramillo, G. Galli, Phys. Rev. B 90 (2014) 155204–155214.
- [11] A. Ziani, E. Nurlaela, D. Dhawale, D. Silva, E. Alarousa, O. Mohammed, K. Takanabe, Phys. Chem. Chem. Phys. 17 (2015) 2670–2677.
- [12] A. Ishikawa, T. Takata, J. Kondo, M. Hara, K. Domen, J. Phys. Chem. B 108 (2004) 11049–11053.
- [13] S. Li, J. Zhang, S. Hu, K. Xu, W. Jing, J. Liu, J. Alloys Compd. 695 (2017) 1137–1144.
- [14] Z. Wang, J. Hou, S. Jiao, K. Huang, H. Zhu, J. Mater. Chem. 22 (2012) 21972–21978.
- [15] I. Narkeviciute, P. Chakthranount, A. Mackus, C. Hahn, B. Pinaud, S. Bent, T. Jaramillo, Nano Lett. 16 (2016) 7565–7572.
- [16] S. Ma, K. Maeda, T. Hisatomi, M. Tabata, A. Kudo, K. Domen, Chem. Eur. J. 19 (2013) 7498-7486.
- [17] M. Zhong, T. Hisatomi, Y. Sasaki, S. Suzuki, K. Teshima, M. Nakabayashi, N. Shibata, H. Nishiyama, M. Katayama, T. Yamada, K. Domen, Angew. Chem. Int. Ed. 56 (2017) 4739–4743.
- [18] G. Liu, J. Shi, F. Zhang, Z. Chen, J. Han, C. Ding, S. Chen, Z. Wang, H. Han, C. Li, Angew. Chem. Int. Ed. 53 (2014) 7295–7299.
- [19] G. Fu, S. Yan, T. Yu, Z. Zou, Appl. Phys. Lett. 107 (2015) 171902-171908.
- [20] E. Nurlaela, M. Harb, S. del Gobbo, M. Vashishta, K. Takanabe, J. Solid State Chem. 229 (2015) 219–227.

- [21] H. Tong, S. Ouyang, Y. Bi, N. Umezawa, M. Oshikiri, J. Ye, Adv. Mater. 24 (2012) 229–251.
- [22] J. Yu, J. Low, W. Xiao, P. Zhou, M. Jaroniec, J. Am. Chem. Soc. 136 (2014) 8839–8842.
- [23] X. Liu, G. Dong, S. Li, G. Lu, Y. Bi, J. Am. Chem. Soc. 138 (2016) 2917–2920.
- [24] R. Li, F. Zhang, D. Wang, J. Yang, M. Li, J. Zhu, X. Zhou, H. Han, C. Li, Nat. Commun. 4 (2013) 1432–1441.
- [25] J. Zhu, F. Fan, R. Chen, H. An, Z. Feng, C. Li, Angew. Chem. Int. Ed. 54 (2015) 9111–9242.
- [26] R. Li, H. Han, F. Zhang, D. Wang, C. Li, Energy Environ. Sci. 7 (2014) 1369–1376.
- [27] L. Mu, Y. Zhao, A. Li, S. Wang, Z. Wang, J. Yang, Y. Wang, T. Liu, R. Chen, J. Zhu, F. Fan, R. Li, C. Li, Energy Environ. Sci. 9 (2016) 2463–2469.
- [28] P. Li, Y. Zhou, Z. Zhao, Q. Xu, X. Wang, M. Xiao, Z. Zou, J. Am. Chem. Soc. 137 (2015) 9547–9550.
- [29] L. Wang, J. Ge, A. Wang, M. Deng, X. Wang, S. Bai, R. Li, J. Jiang, Q. Zhang, Y. Luo, Y. Xiong, Angew. Chem. Int. Ed. 53 (2014) 5107–5211.
- [30] H. Yang, C. Sun, S. Qiao, J. Zou, G. Liu, S. Smith, H. Cheng, G. Lu, Nature 453 (2008) 638–641.
- [31] S. Ma, T. Hisatomi, K. Maeda, Y. Moriya, K. Domen, J. Am. Chem. Soc. 134 (2012) 19993–19996.
- [32] Y. He, J. Thorne, C. Wu, P. Ma, C. Du, Q. Dong, J. Guo, D. Wang, Chem 1 (2016) 640–655.
- [33] L. Wang, X. Zhou, N. Nguyen, I. Hwang, P. Schmuki, Adv. Mater. 28 (2016) 2432–2438.
- [34] M. Xiao, B. Luo, M. Lyu, S. Wang, L. Wang, Adv. Energy Mater. 17 (2017) 1605–1608.
- [35] Y. Li, L. Zhang, A. Torres-Pardo, J.M. González-Calbet, Y. Ma, P. Oleynikov, O. Terasaki, S. Asahina, M. Shima, D. Cha, L. Zhao, K. Takanabe, J. Kubota, K. Domen, Nat. Commun. 4 (2013) 1–7.
- [36] S. Suzuki, K. Teshima, K. Yubuta, S. Ito, Y. Moriga, T. Takata, T. Shishido, K. Domen, CrystEngComm 14 (2012) 7178–7183.
- [37] S. Suzuki, H. Wagata, M. Komatsus, T. Minegishi, K. Domen, S. Oishi, K. Teshima, J. Mater. Chem. A 3 (2015) 13946–13952.
- [38] D. Lu, M. Hara, T. Hisatomi, T. Takata, K. Domen, J. Phys. Chem. C 113 (2009) 17151–17155.
- [39] S. Chen, S. Shen, G. Liu, Y. Qi, F. Zhang, C. Li, Angew. Chem. Int. Ed. 54 (2015) 3047–3051.
- [40] S. Yan, S. Ouyang, J. Gao, M. Yang, J. Feng, X. Fan, L. Wan, Z. Li, J. Ye, Y. Zhou, Z. Zou, Angew. Chem. Int. Ed. 122 (2010) 6544–6549.
- [41] M. Tahir, N.S. Amin, Sustain. Energy Rev. 25 (2013) 560-579.
- [42] M.S. Hamdy, R. Amrollahi, I. Sinev, B. Mei, G. Mul, J. Am. Chem. Soc. 136 (2014) 594–597.
- [43] S. Gao, Y. Lin, X. Jiao, Y. Sun, Q. Luo, W. Zhang, D. Li, J. Yang, Y. Xie, Nature 529 (2016) 68–71.
- [44] M. Higashi, K. Domen, R. Abe, Energy Environ. Sci. 4 (2011) 4138-4147.
- [45] H. Li, Y. Gao, Y. Zhou, F. Fan, Q. Han, Q. Xu, X. Wang, M. Xiao, C. Li, Z. Zou, Nano Lett. 16 (2016) 5547–5552.
- [46] M. Ritala, P. Kalsi, D. Riihela, K. KuKli, M. Leskela, J. Jokinen, J. Chem. Mater. 11 (1999) 1712–1718.
- [47] S. Henderson, A. Hector, J. Solid State Chem. 179 (2006) 3518-3524.
- [48] J. Wang, J. Feng, L. Zhang, Z. Li, Z. Zou, Phys. Chem. Chem. Phys. 16 (2014) 15375–15380.
- [49] W. Chun, A. Ishikawa, H. Fujisawa, T. Takata, J. Kondo, M. Hara, M. Kawai, Y. Matsumoto, J. Phys. Chem. B 107 (2003) 1798–1803.